



SHENZHEN JTD ELECTRONICS CO.,LTD

TO-92 Plastic-Encapsulate Transistors

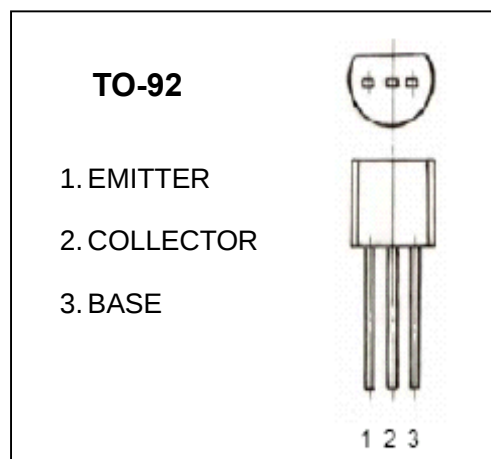
13001S8D TRANSISTOR(NPN)

FEATURES

Power switching applications

LIMITING VALUES(T_j=25℃ Unless Otherwise Stated)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	600	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EB0}	7	V
Collector Current	I _c	0.5	A
Total Power Dissipation	P _c	0.65	W
Storage Temperature	T _{stg}	-65~150	℃
Junction Temperature	T _j	150	℃



ELECTRICAL CHARACTERISTICS (T_j=25℃ Unless Otherwise Stated)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c =0.5mA, I _e =0	600		V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c =10mA, I _b =0	400		V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _e =1mA, I _c =0	7		V
Collector-Base Cutoff Current	I _{CB0}	V _{cb} =600V, I _e =0		100	μ A
Collector- Emitter Cutoff Current	I _{CEO}	V _{ce} =400V, I _b =0		20	μ A
Emitter-Base Cutoff Current	I _{EBO}	V _{eb} =7V, I _c =0		100	μ A
DC Current Gain	h _{FE}	V _{ce} =20V, I _c =20mA	10	40	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _c =200mA, I _b =100mA		0.6	V
Base- Emitter Saturation Voltage	V _{BE(sat)}	I _c =200mA, I _b =100mA		1.2	V
Storage Time	T _s	I _c =0.1mA, (UI9600)		2	μ S
Falling Time	f _T	V _{CE} =20V, I _c =20mA f=1MHZ		0.8	μ S

CLASSIFICATION OF H_{fe}(1)

Range	10-15	15-20	20-25	30-35
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